**Product data sheet** 

### 1. General description

The GTL2018 is an octal translating transceiver designed for 3.3 V LVTTL system interface with a GTL–/GTL/GTL+ bus.

The direction pin (DIR) allows the part to function as either a GTL-to-LVTTL sampling receiver or as an LVTTL-to-GTL interface.

The GTL2018 LVTTL inputs (only) are tolerant up to 5.5 V, allowing direct access to TTL or 5 V CMOS inputs.

### 2. Features and benefits

- Operates as an octal GTL-/GTL/GTL+ sampling receiver or as an LVTTL to GTL-/GTL/GTL+ driver
- 3.0 V to 3.6 V operation with 5 V tolerant LVTTL input
- GTL input and output 3.6 V tolerant
- V<sub>ref</sub> adjustable from 0.5 V to 0.5V<sub>CC</sub>
- Partial power-down permitted
- Latch-up protection exceeds 100 mA per JESD78
- ESD protection exceeds 2000 V HBM per JESD22-A114 and 1000 V CDM per JESD22-CC101
- AEC-Q100 compliance available
- Package offered: TSSOP24

### 3. Quick reference data

#### Table 1.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>i</sub>	input capacitance	control inputs; V <sub>I</sub> = 3.0 V or 0 V	-	2	2.5	pF
Cio	input/output capacitance	A port; $V_0 = 3.0$ V or 0 V	-	4.6	6	pF
		B port; $V_0 = V_{TT}$ or 0 V	-	3.4	4.3	pF
GTL; V <sub>ref</sub> =	= 0.8 V; V <sub>TT</sub> = 1.2 V					
t <sub>PLH</sub>	LOW to HIGH propagation delay	An to Bn; see Figure 3	-	2.8	5	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	An to Bn; see Figure 3	-	3.4	7	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	Bn to An; see Figure 4	-	5.2	8	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	Bn to An; see Figure 4	-	4.9	7	ns



#### **Ordering information** 4.

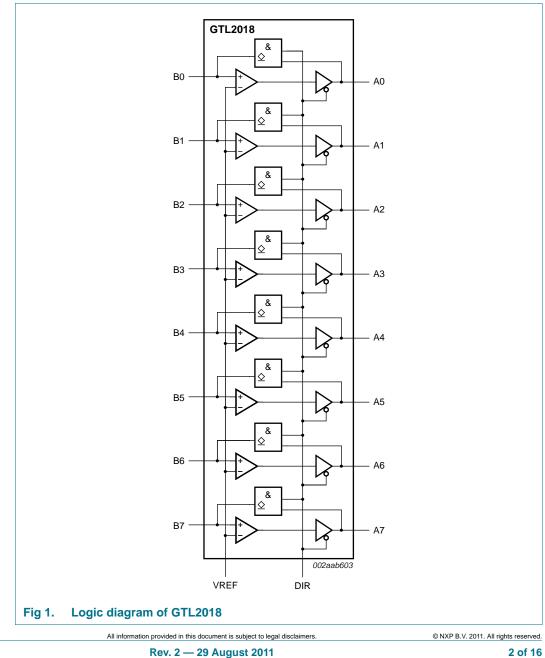
#### Table 2. **Ordering information**

 $T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C.$ 

Type number	Topside mark	Package			
		Name	Description	Version	
GTL2018PW	GTL2018PW	TSSOP24	plastic thin shrink small outline package; 24 leads;	SOT355-1	
GTL2018PW/Q900[1]			body width 4.4 mm		

[1] GTL2018PW/Q900 is AEC-Q100 compliant. Contact i2c.support@nxp.com for PPAP.

#### 5. **Functional diagram**



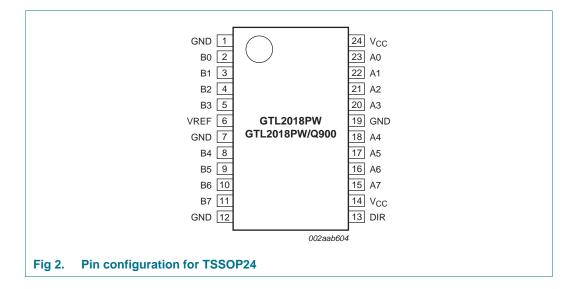


**Product data sheet** 

8-bit LVTTL to GTL transceiver

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
GND	1, 7, 12, 19	ground (0 V)
B0	2	data inputs/outputs (B side, GTL)
B1	3	
B2	4	
B3	5	
B4	8	
B5	9	
B6	10	
B7	11	
VREF	6	GTL reference voltage
DIR	13	direction control input (LVTTL)
V <sub>CC</sub>	14, 24	positive supply voltage
A7	15	data inputs/outputs (A side, LVTTL)
A6	16	
A5	17	
A4	18	
A3	20	
A2	21	
A1	22	
A0	23	

GTL2018

### 7. Functional description

Refer to Figure 1 "Logic diagram of GTL2018".

### 7.1 Function table

Table 4.Function tableH = HIGH voltage level; L = LOW voltage level.				
Input	Input/output			
DIR	An (LVTTL)	Bn (GTL)		
н	input	Bn = An		
L	An = Bn	input		

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Voltages are referenced to GND (ground = 0 V).

	(3)	/-			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-	-50	mA
VI	input voltage	A port	-0.5 <mark>[1]</mark>	7.0	V
		B port	-0.5 <mark>[1]</mark>	4.6	V
I <sub>OK</sub>	output clamping current	$V_{O} < 0 V$	-	-50	mA
Vo	output voltage	output in OFF or HIGH state; A port	-0.5 <sup>[1]</sup>	7.0	V
		output in OFF or HIGH state; B port	-0.5 <u>[1]</u>	4.6	V
I <sub>OL</sub>	LOW-level output current	A port	[2] _	32	mA
		B port	[2]	80	mA
I <sub>OH</sub>	HIGH-level output current	A port	[3] _	-32	mA
T <sub>stg</sub>	storage temperature		<u>[4]</u> –60	+150	°C
·sig			_ 00		U

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] Current into any output in the LOW state.

[3] Current into any output in the HIGH state.

[4] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150 °C.

8-bit LVTTL to GTL transceiver

## 9. Recommended operating conditions

Table 6.	Recommended operation	ating conditions <sup>[1]</sup>				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		3.0	-	3.6	V
V <sub>TT</sub>	termination voltage <sup>[2]</sup>	GTL-	0.85	0.9	0.95	V
		GTL	1.14	1.2	1.26	V
		GTL+	1.35	1.5	1.65	V
V <sub>ref</sub> reference voltage	reference voltage	overall	0.5	$^{2}$ <sub>3</sub> V <sub>TT</sub>	$0.5V_{CC}$	V
		GTL-	0.5	0.6	0.63	V
		GTL	0.76	0.8	0.84	V
		GTL+	0.87	1.0	1.10	V
VI	input voltage	B port	0	$V_{TT}$	3.6	V
		except B port [3]	0	3.3	5.5	V
V <sub>IH</sub>	HIGH-level input voltage	B port	V <sub>ref</sub> + 0.050	-	-	V
		except B port	2	-	-	V
V <sub>IL</sub>	LOW-level input	B port	-	-	$V_{ref} - 0.050$	V
	voltage	except B port	-	-	0.8	V
I <sub>OH</sub>	HIGH-level output current	A port	-	-	-16	mA
I <sub>OL</sub>	LOW-level output	B port	-	-	40	mA
	current	A port	-	-	16	mA
T <sub>amb</sub>	ambient temperature	operating in free air	-40	-	+85	°C

[1] Unused inputs must be held HIGH or LOW to prevent them from floating.

[2]  $V_{TT}$  maximum of 3.6 V with resistor sized to so  $I_{OL}$  maximum is not exceeded.

[3] A0 to A7  $V_{I(max)}$  is 3.6 V if configured as outputs (DIR = LOW).

### **10. Static characteristics**

#### Table 7. Static characteristics

Recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = -40$  °C to +85 °C.

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
V <sub>OH</sub> HIGH-level output		A port; V_{CC} = 3.0 V to 3.6 V; $I_{OH}$ = –100 $\mu A$	[2] V <sub>CC</sub> – 0.2	-	-	V
	voltage	A port; $V_{CC}$ = 3.0 V; $I_{OH}$ = -16 mA	2 2.0	-	-	V
V <sub>OL</sub>	LOW-level output	B port; $V_{CC}$ = 3.0 V; $I_{OL}$ = 40 mA	[2] _	0.23	0.4	V
	voltage	A port; $V_{CC}$ = 3.0 V; $I_{OL}$ = 8 mA	[2] _	0.28	0.4	V
		A port; $V_{CC}$ = 3.0 V; $I_{OL}$ = 12 mA	[2] _	0.40	0.55	V
		A port; $V_{CC}$ = 3.0 V; $I_{OL}$ = 16 mA	[2] _	0.55	0.8	V
lı	input current	control inputs; $V_{CC} = 3.6 \text{ V}$ ; $V_I = V_{CC}$ or GND	-	-	±1	μΑ
		B port; $V_{CC}$ = 3.6 V; $V_{I}$ = $V_{TT}$ or GND	-	-	±1	μA
		A port; $V_{CC}$ = 0 V or 3.6 V; $V_{I}$ = 5.5 V	-	-	10	μA
		A port; $V_{CC}$ = 3.6 V; $V_{I}$ = $V_{CC}$	-	-	±1	μA
		A port; $V_{CC} = 3.6 \text{ V}; V_{I} = 0 \text{ V}$	-	-	-5	μA
I <sub>OZ</sub>	off-state output current	A port; $V_{CC} = 0$ V; $V_{I}$ or $V_{O} = 0$ V to 3.6 V	-	-	±100	μΑ
I <sub>CC</sub>	supply current	A port; $V_{CC}$ = 3.6 V; $V_I$ = $V_{CC}$ or GND; $I_O$ = 0 mA	-	8	12	mA
		B port; $V_{CC}$ = 3.6 V; $V_I$ = $V_{TT}$ or GND; $I_O$ = 0 mA	-	8	12	mA
∆l <sub>CC</sub> [3]	additional supply current	per input; A port or control inputs; $V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = V_{CC} - 0.6 \text{ V}$	-	-	500	μΑ
Ci	input capacitance	control inputs; $V_I = 3.0 \text{ V} \text{ or } 0 \text{ V}$	-	2	2.5	pF
Cio	input/output	A port; $V_0 = 3.0$ V or 0 V	-	4.6	6	pF
	capacitance	B port; $V_0 = V_{TT}$ or 0 V	-	3.4	4.3	pF

[1] All typical values are measured at V\_{CC} = 3.3 V and T\_{amb} = 25 °C.

[2] The input and output voltage ratings my be exceeded if the input and output current ratings are observed.

[3] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

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## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

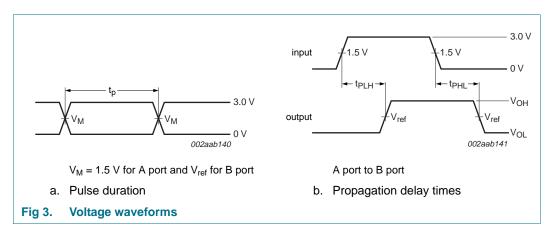
 $V_{\rm CC} = 3.3 \ V \pm 0.3 \ V.$ 

Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
= 0.6 V; V <sub>TT</sub> = 0.9 V					
LOW to HIGH propagation delay	An to Bn; see Figure 3	-	2.8	5	ns
HIGH to LOW propagation delay	An to Bn; see Figure 3	-	3.3	7	ns
LOW to HIGH propagation delay	Bn to An; see Figure 4	-	5.3	8	ns
HIGH to LOW propagation delay	Bn to An; see Figure 4	-	5.2	8	ns
= 0.8 V; V <sub>TT</sub> = 1.2 V					
LOW to HIGH propagation delay	An to Bn; see Figure 3	-	2.8	5	ns
HIGH to LOW propagation delay	An to Bn; see Figure 3	-	3.4	7	ns
LOW to HIGH propagation delay	Bn to An; see Figure 4	-	5.2	8	ns
HIGH to LOW propagation delay	Bn to An; see Figure 4	-	4.9	7	ns
= 1.0 V; V <sub>TT</sub> = 1.5 V					
LOW to HIGH propagation delay	An to Bn; see Figure 3	-	2.8	5	ns
HIGH to LOW propagation delay	An to Bn; see Figure 3	-	3.4	7	ns
LOW to HIGH propagation delay	Bn to An; see Figure 4	-	5.1	8	ns
HIGH to LOW propagation delay	Bn to An; see Figure 4	-	4.7	7	ns
	= 0.6 V; $V_{TT}$ = 0.9 V LOW to HIGH propagation delay HIGH to LOW propagation delay LOW to HIGH propagation delay HIGH to LOW propagation delay = 0.8 V; $V_{TT}$ = 1.2 V LOW to HIGH propagation delay HIGH to LOW propagation delay LOW to HIGH propagation delay HIGH to LOW propagation delay LOW to HIGH propagation delay HIGH to LOW propagation delay	= 0.6 V; $V_{TT}$ = 0.9 VLOW to HIGH propagation delayAn to Bn; see Figure 3HIGH to LOW propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayBn to An; see Figure 4HIGH to LOW propagation delayBn to An; see Figure 4= 0.8 V; $V_{TT}$ = 1.2 VLOW to HIGH propagation delayAn to Bn; see Figure 3HIGH to LOW propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 4= 0.8 V; $V_{TT}$ = 1.2 VLOW to HIGH propagation delayLOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayBn to An; see Figure 4= 1.0 V; $V_{TT}$ = 1.5 VLOW to HIGH propagation delayLOW to HIGH propagation delayAn to Bn; see Figure 3HIGH to LOW propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 4	= 0.6 V; $V_{TT} = 0.9 V$ LOW to HIGH propagation delayAn to Bn; see Figure 3HIGH to LOW propagation delayAn to Bn; see Figure 4LOW to HIGH propagation delayBn to An; see Figure 4HIGH to LOW propagation delayBn to An; see Figure 4= 0.8 V; $V_{TT} = 1.2 V$ LOW to HIGH propagation delayAn to Bn; see Figure 3= 0.8 V; $V_{TT} = 1.2 V$ LOW to HIGH propagation delayAn to Bn; see Figure 3HIGH to LOW propagation delayAn to Bn; see Figure 4LOW to HIGH propagation delayBn to An; see Figure 4HIGH to LOW propagation delayBn to An; see Figure 4HIGH to LOW propagation delayAn to Bn; see Figure 4HIGH to LOW propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 3LOW to HIGH propagation delayAn to Bn; see Figure 4LOW to HIGH propagation delayAn to Bn; see Figure 4	= 0.6 V; $V_{TT} = 0.9 V$ LOW to HIGH propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 3-3.3LOW to HIGH propagation delayBn to An; see Figure 4-5.3HIGH to LOW propagation delayBn to An; see Figure 4-5.2 <b>0.8 V; V</b> <sub>TT</sub> = 1.2 VVLOW to HIGH propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 4-5.2 <b>1.0</b> V; V <sub>TT</sub> = 1.5 VEn to An; see Figure 4-5.2LOW to HIGH propagation delayAn to Bn; see Figure 4-4.9 <b>1.0</b> V; V <sub>TT</sub> = 1.5 VEOW to HIGH propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 3-2.8LOW to HIGH propagation delayAn to Bn; see Figure 4-5.1LOW to HIGH propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 3-2.8HIGH to LOW propagation delayAn to Bn; see Figure 3-2.8LOW to HIGH propagation delayAn to Bn; see Figure 4-5.1	= 0.6 V; V <sub>TT</sub> = 0.9 VLOW to HIGH propagation delayAn to Bn; see Figure 3-2.85HIGH to LOW propagation delayAn to Bn; see Figure 3-3.37LOW to HIGH propagation delayBn to An; see Figure 4-5.38HIGH to LOW propagation delayBn to An; see Figure 4-5.28 <b>0.8 V; V<sub>TT</sub> = 1.2 V</b> EEEELOW to HIGH propagation delayAn to Bn; see Figure 3-2.85HIGH to LOW propagation delayAn to Bn; see Figure 3-3.47LOW to HIGH propagation delayBn to An; see Figure 4-5.28HIGH to LOW propagation delayBn to An; see Figure 3-2.85HIGH to LOW propagation delayBn to An; see Figure 4-5.28UOW to HIGH propagation delayBn to An; see Figure 4-4.97= 1.0 V; V <sub>TT</sub> = 1.5 VEEEE1.0LOW to HIGH propagation delayAn to Bn; see Figure 3-2.85HIGH to LOW propagation delayAn to Bn; see Figure 3-2.85HIGH to LOW propagation delayAn to Bn; see Figure 3-2.85LOW to HIGH propagation delayAn to Bn; see Figure 3-2.85HIGH to LOW propagation delayAn to Bn; see Figure 4-5.18LOW to HIGH propagation delayBn to An; see Figure 4-5.18

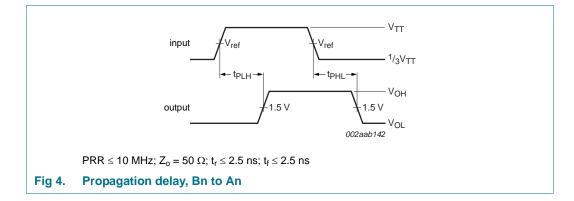
[1] All typical values are at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

#### 11.1 Waveforms

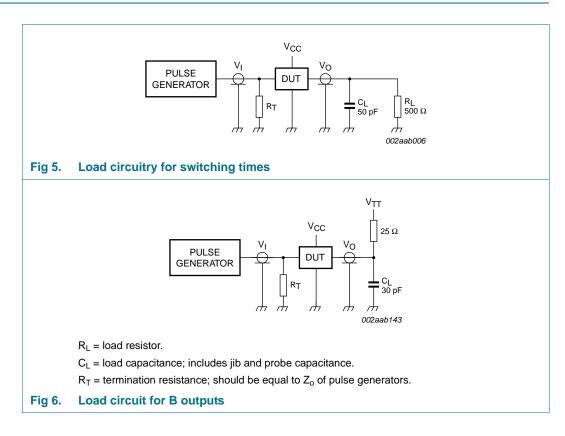
 $V_M$  = 1.5 V at  $V_{CC} \ge 3.0$  V;  $V_M$  = 0.5V\_{CC} at  $V_{CC} \le 2.7$  V for A ports and control pins;  $V_M$  =  $V_{ref}$  for B ports.



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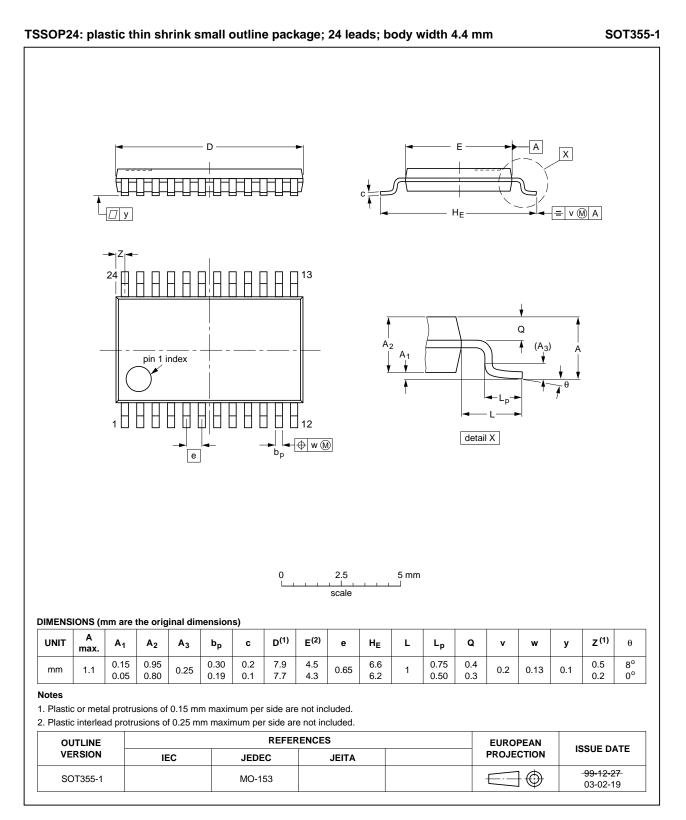


## **12. Test information**



8-bit LVTTL to GTL transceiver

### 13. Package outline



#### Fig 7. Package outline SOT355-1 (TSSOP24)

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### 14. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365* "Surface mount reflow soldering description".

#### 14.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

### 14.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- · Board specifications, including the board finish, solder masks and vias
- · Package footprints, including solder thieves and orientation
- · The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

#### 14.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- · Solder bath specifications, including temperature and impurities

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#### 14.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see <u>Figure 8</u>) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 9 and 10

#### Table 9. SnPb eutectic process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)		
	Volume (mm <sup>3</sup> )		
	< 350	≥ 350	
< 2.5	235	220	
≥ 2.5	220	220	

#### Table 10. Lead-free process (from J-STD-020C)

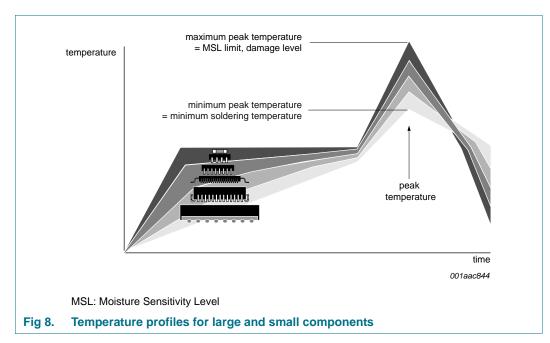
Package thickness (mm)	Package reflow temperature (°C)			
	Volume (mm <sup>3</sup> )			
	< 350	350 to 2000	> 2000	
< 1.6	260	260	260	
1.6 to 2.5	260	250	245	
> 2.5	250	245	245	

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 8.

8-bit LVTTL to GTL transceiver

**GTL2018** 



For further information on temperature profiles, refer to Application Note *AN10365 "Surface mount reflow soldering description"*.

### **15. Abbreviations**

Table 11.	Abbreviations
Acronym	Description
CDM	Charged-Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
GTL	Gunning Transceiver Logic
HBM	Human Body Model
LVTTL	Low Voltage Transistor-Transistor Logic
PRR	Pulse Repetition Rate
TTL	Transistor-Transistor Logic

# 16. Revision history

Table 12. Revisi	ion history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
GTL2018 v.2	20110829	Product data sheet	-	GTL2018 v.1
Modifications: • Section 2 "Features and benefits":				
<ul> <li>6th bullet item corrected from "exceeds 500 mA per JESD78" to "exceeds 100 mA per JESD78"</li> </ul>				
<ul> <li>7th bullet item: removed phrase "200 V MM per JESD22-A115"</li> </ul>				
	<ul> <li>added (ne</li> </ul>	ew) 8th bullet item "AEC-Q10	0 compliance available"	
	Table 2 "Ord	ering information":		
	<ul> <li>added typ</li> </ul>	e number GTL2018PW/Q90	0	
	<ul> <li>added <u>Ta</u></li> </ul>	ble note [1]		
	<ul> <li>Figure 2 "Pir</li> </ul>	configuration for TSSOP24"	modified: added type num	nber GTL2018PW/Q900
GTL2018 v.1	20070215	Product data sheet	-	-

### 17. Legal information

#### 17.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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Product data sheet

#### 8-bit LVTTL to GTL transceiver

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Date of release: 29 August 2011 Document identifier: GTL2018